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12.10. (Twice amended) A semiconductor processing method, comprising:
depositing a layer of material comprising silicon and oxygen, as initially deposited, over a substrate;
exposing some portions of the layer to energy while leaving other portions unexposed, the exposing altering physical properties of the exposed portions relative to the unexposed portions; and
after the exposing, subjecting the exposed and unexposed portions of the layer to common conditions, the common conditions being effective to remove the silicon-comprising material and comprising a rate of removal that is influenced by the altered physical properties of the layer, the common conditions removing either the exposed or unexposed portions faster than the other of the exposed and unexposed portions.

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24.22. (Once amended) A semiconductor processing method, comprising:
depositing a layer comprising $(CH_3)_ySi(OH)_{4-y}$, as initially deposited, with y being greater than 0 and less than 4, over a substrate;
exposing some portions of the layer to ultraviolet light while leaving other portions unexposed, the exposing converting the exposed portions to $(CH_3)_xSiO_{2-x}$, with x being greater than 0 and less than 2; and
after the exposing, subjecting the exposed and unexposed portions of the layer to hydrofluoric acid to selectively remove the $(CH_3)_ySi(OH)_{4-y}$ of the unexposed portions relative to the $(CH_3)_xSiO_{2-x}$ of the exposed portions.

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~~27.25. (Once amended) A semiconductor processing method, comprising:~~

~~depositing a layer comprising Si(OH)₄, as initially deposited, over a substrate;~~

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~~exposing some portions of the layer to energy while leaving other portions unexposed, the exposing converting the exposed portions to SiO₂; and~~

~~after the exposing, subjecting the exposed and unexposed portions of the layer to hydrofluoric acid to selectively remove the Si(OH)₄ of the unexposed portions relative to the SiO₂ of the exposed portions.~~

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~~30. (Once amended) The method of claim 1 wherein the forming a layer comprises depositing a layer of material comprising oxygen, as initially deposited.~~

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~~10. 31. (Once amended) The method of claim 1 wherein the forming a layer comprises depositing a layer of material comprising (CH₃)_ySi(OH)_{4-y}, as initially deposited, with y being greater than 0 and less than 4.~~

~~II. 32. (Once amended) The method of claim 1 wherein the forming a layer comprises depositing a layer of material comprising Si(OH)₄, as initially deposited.~~